





eGuard0522P TVS Arrays

Description - eGuard™

The eGuard0522P* is an ultra low capacitance TVS (Transient Voltage Suppressor) array designed to protect sensitive semiconductor components from electrical overstress when interfaced to high-speed data lines. The ultra low capacitance (0.35pF typical I/O to I/O) of the eGuard0522P ensures negligible signal attenuation at data rates up to 3.5GHz. The solid-state construction ensures fast clamping of electrical overstress transients resulting from ESD (electrostatic discharge), EFT (Electrical Fast Transients) or CDE (Cable Discharge Events).

In addition to ultra low capacitance, the eGuard0522P provides superior surge current capability and excellent voltage clamping performance. The surge current capability (8x20µs) is rated at 7A; approximately 33% higher than industry norms. Furthermore, the tight clamping ratio (VC/VRWM) of 1.9 (typical at 1A) ensures harmful transients are clamped quickly and close to the normal working voltage of the circuit. The super tight clamping ratio is 30% better than industry norms and ensures superior protection of sensitive integrated circuits.

The eGuard0522P is designed to protect up to two data lines. It is packaged in a RoHS/WEEE compliant, 6 pin DFN that has a very low package profile of 0.55mm (nominal). The combination of ultra low capacitance, high surge capability, tight clamping ratio and low package profile make the eGuard0522P the ideal choice for today's ESD sensitive, space constrained applications.

Features

- ESD protection in accordance with:
 IEC 61000-4-2 (ESD) ±17kV (air), ±12kV (contact)
 IEC 61000-4-5 (lightning) 7A (8/20µs)
 IEC 61000-4-4 (EFT) 40A (5/50ns)
- Tight clamping ratio, V_C/V_{RWM}, ensures superior protection
- High reverse surge current, IPP, capability
- Low idle current minimizes standby power consumption
- Low profile DFN package
- Package design optimized for high speed lines
- Flow-Through design
- Protects two I/O lines
- Low capacitance: 0.35pF typical (I/O to I/O)
- Low operating voltage: 5V
- Solid-state silicon-avalanche technology

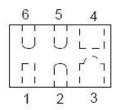
Mechanical Characteristics

- DFNWB1.6×1-6L 6-pin package(1.6×1.0×0.5mm)
- Pb-Free, Halogen Free, RoHS/WEEE Compliant
- Lead Pitch: 0.5mm
- Lead finish: NiPdAu
- Marking: Marking Code
- Packaging: Tape and Reel

Applications

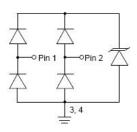
- High Definition Multi-Media Interface (HDMI)
- Digital Visual Interface (DVI)
- DisplayPort TM Interface
- MDDI(Mobile Display Digital Interface)Ports
- PCI(Peripheral Component Interconnect) Express
- eSATA(External Serial Advanced Technology Attachment)Interfaces

Pin Configuration



Pin	Identification			
1, 2	Input Lines			
5, 6	Output Lines (No Internal Connection)			
3, 4	Ground			

Circuit Diagram



- * The e Guard logo is a trademark of SMC Diode Solutions Sangdest Microelectronics (Nanjing) Co.
 - China Germany Korea Singapore United States
 - http://www.smc-diodes.com
 sales@ smc-diodes.com







Ordering Information

Device	Package	Shipping	
eGuard0522P	DFNWB1.6×1-6L	3000pcs / reel	
eGuaru0522P	(Pb-Free)	3000pcs / reer	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Maximum Ratings @TA=25°C unless otherwise specified

Parameter	Symbol	Value	Units
Peak Pulse Current (tp=8/20µs)	I _{PP}	7	Α
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V _{ESD}	±17 ±12	kV
Operating Junction Temperature Range	T_J	-55 to + 150	°C
Storage Temperature Range	T _{STG}	-55 to + 150	°C

Electrical Characteristics

Characteristics	Symbol	Condition	Min.	Тур.	Max.	Units
Reverse Stand-Off Voltage	V_{RWM}	Any I/O pin to ground	-	-	5	V
Reverse Breakdown Voltage	V_{BR}	@ I _t =1mA Any I/O pin to ground	6	-	-	V
Forward Voltage Drop	V _F	@ I _F =1mA, T = 25 ℃	-	-	0.9	V
Reverse Leakage Current	I _R	@V _{RWM} = 5V, T = 25 ℃ Any I/O pin to ground	-	0.5	1	μΑ
Clamping Voltage	Vc	@I _{PP} = 1A, tp=8/20µs Any I/O pin to ground	-	9.5	10.5	V
Clamping Voltage	Vc	@I _{PP} = 7A, tp=8/20µs Any I/O pin to ground	-	-	17	V
Junction Capacitance	C _j	@V _R = 0V, f _{SIG} = 1MHz Between I/O pins	-	0.35	0.4	pF
Junction Capacitance	C _j	@V _R = 0V, f _{SIG} = 1MHz Any I/O pin to ground	-	0.65	0.8	pF

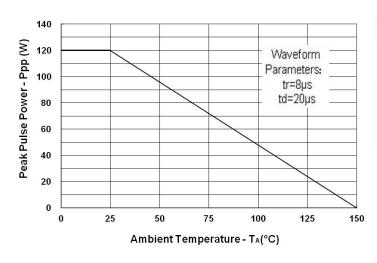
 $^{^{\}star}\,$ Pulse width < 300 $\mu s,\,$ duty cycle < 2%







Ratings and Characteristics Curves



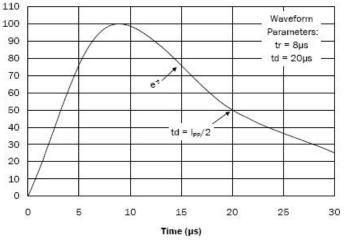
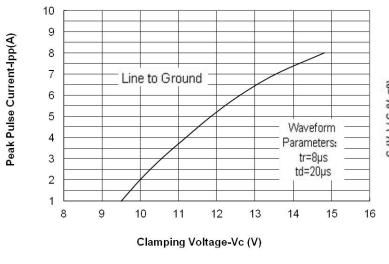


Fig.1 Power Derating Curve

Fig.2 Pulse Waveform



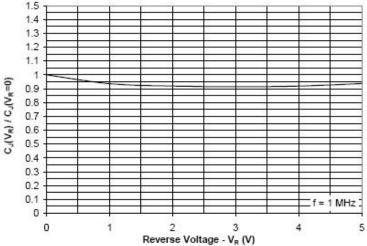


Fig. 3 Clamping Voltage vs. Peak Pulse Current

Fig. 4 Normalized Capacitance vs. Reverse Voltage

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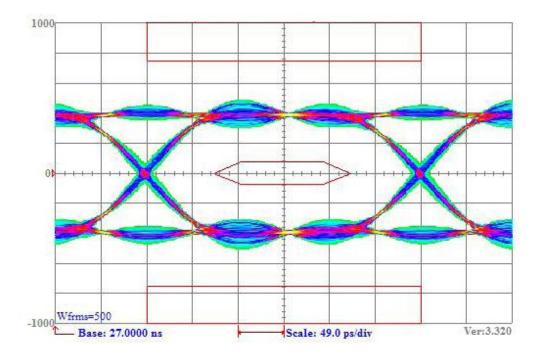


Fig. 5 HDMI 1.4 Eye Diagram

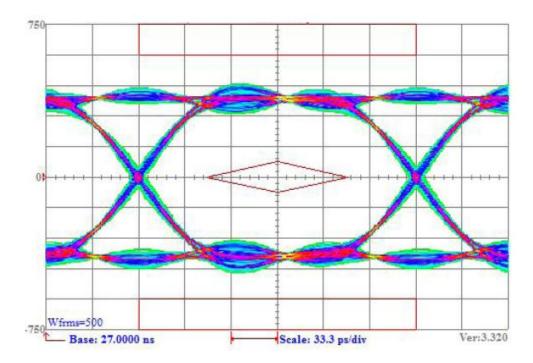


Fig. 6 USB3.0 Eye Diagram

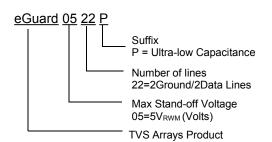
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Part Name Information



Marking Diagram

522P X

Where 522P is eGuard0522P

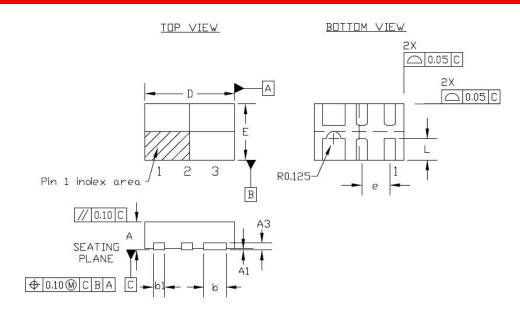
522P = Part name

X = Marking code for date code

Cautions: Molding resin

Epoxy resin UL:94V-0

Mechanical Dimensions DFNWB1.6×1-6L



SYMBOL	COMMON					
	DIMENSIONS MILLIMETER			DIMENSIONS INCH		
2 -	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.45	0.50	0.55	0.018	0.020	0.022
A1	0.00	0.02	0.05	0.000	0.001	0.002
АЗ	0.125 REF			0.005 REF		
b	0.35	0.40	0.45	0.014	0.016	0.018
b1	0.15	0.20	0.25	0.006	0.008	0.010
D	1,55	1.60	1.65	0.062	0.063	0.065
DS	95 	1000	-	8,00	_	(-8)
Ε	0.95	1.00	1.05	0.038	0,040	0.042
E2	97-2-	124	6/4	8 2	=	12
е	0.50 REF			(0.020 REF	
L	0.33	0.38	0.43	0.013	0.015	0.017

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